

## NCE P-Channel Enhancement Mode Power MOSFET

#### Description

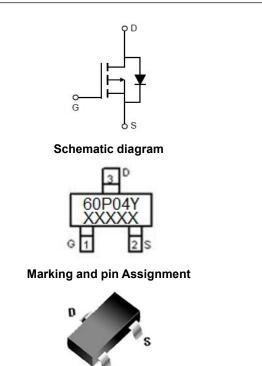
The NCE60P04Y uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge .This device is well suited for use as a load switch or in PWM applications.

#### **General Features**

- V<sub>DS</sub> =-60V,I<sub>D</sub> =-4A
  R<sub>DS(ON)</sub> <120mΩ @ V<sub>GS</sub>=-10V
  - $R_{\text{DS(ON)}}\,{<}170m\Omega$  @ V\_GS=-4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

## Application

- Load switch
- PWM application



SOT-23-3L top view

#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
60P04Y	NCE60P04Y	SOT-23-3L	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Limit	Unit			
VDS	-60	V			
Vgs	±20	V			
Ι <sub>D</sub>	-4	А			
I <sub>DM</sub>	-16	А			
PD	1.5	W			
E <sub>AS</sub>	72	mJ			
TJ,TSTG	-55 To 150	°C			
·					
R <sub>0JA</sub>	83.3	°C/W			
	VDS VGS ID IDM PD EAS TJ,TSTG	VDS      -60        VGS      ±20        ID      -4        IDM      -16        PD      1.5        EAS      72        TJ,TSTG      -55 To 150			

## Electrical Characteristics (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-60	-	-	V	
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-60V,V <sub>GS</sub> =0V	-	-	-1	μA	
Gate-Body Leakage Current	Igss	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA	



On Characteristics (Note 3)						
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-1.0	-1.5	-2.5	V
	R <sub>DS(ON)</sub> -	$V_{GS}$ =-10V, I <sub>D</sub> =-4A	-	106	120	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	-	135	170	mΩ
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4A	-	10	-	S
Dynamic Characteristics (Note4)	····					
Input Capacitance	C <sub>lss</sub>	)/ - 20)/// -0)/	-	930	-	PF
Output Capacitance	Coss	$V_{DS}$ =-30V, $V_{GS}$ =0V,	-	85	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	35	-	PF
Switching Characteristics (Note 4)	I					
Turn-on Delay Time	t <sub>d(on)</sub>		-	8	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =-30V, RL=7.5 $\Omega$ ,	-	4	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{G}$ =3 $\Omega$	-	32	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Qg	V 001 44	-	25	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-30,I <sub>D</sub> =-4A,	-	3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =-10V	-	7	-	nC
Drain-Source Diode Characteristics	II					
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =-4A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-4	Α
Reverse Recovery Time	trr	TJ = 25°C, IF =- 4A	-	25		nS
Reverse Recovery Charge	Qrr	di/dt = -100A/µs <sup>(Note3)</sup>	-	31		nC

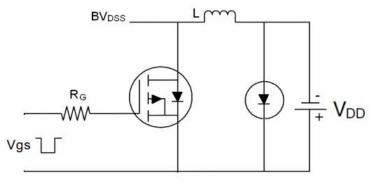
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production 5. EAS condition : Tj=25 $^{\circ}$ C,V<sub>DD</sub>=-20V,V<sub>G</sub>=-10V,L=0.5mH,Rg=25 $\Omega$

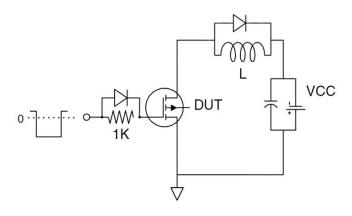


## Test Circuit

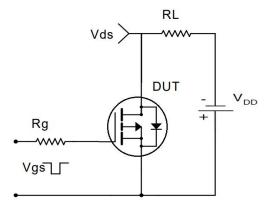
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

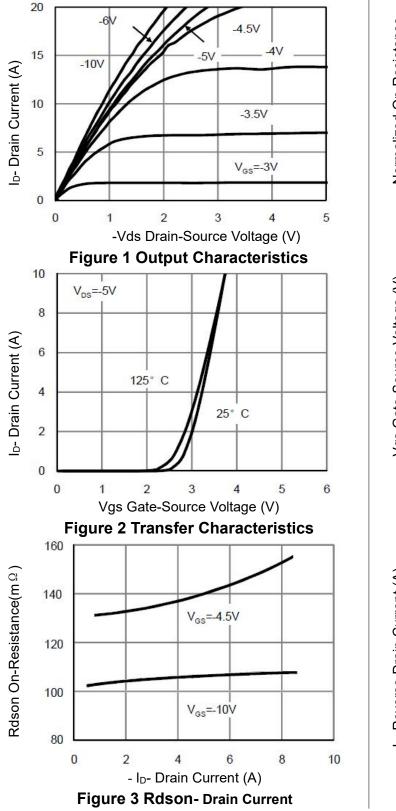


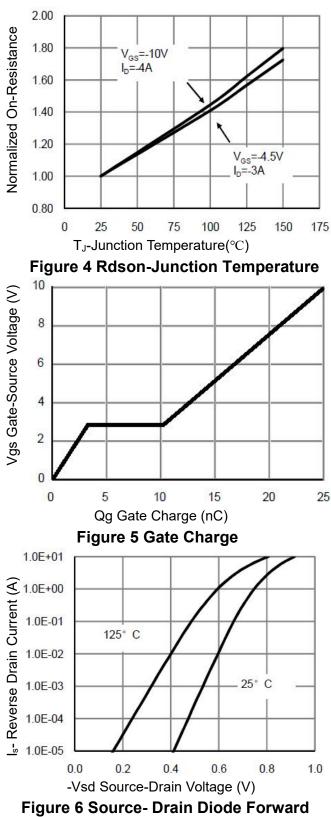
## 3) Switch Time Test Circuit





## **Typical Electrical and Thermal Characteristics (Curves)**

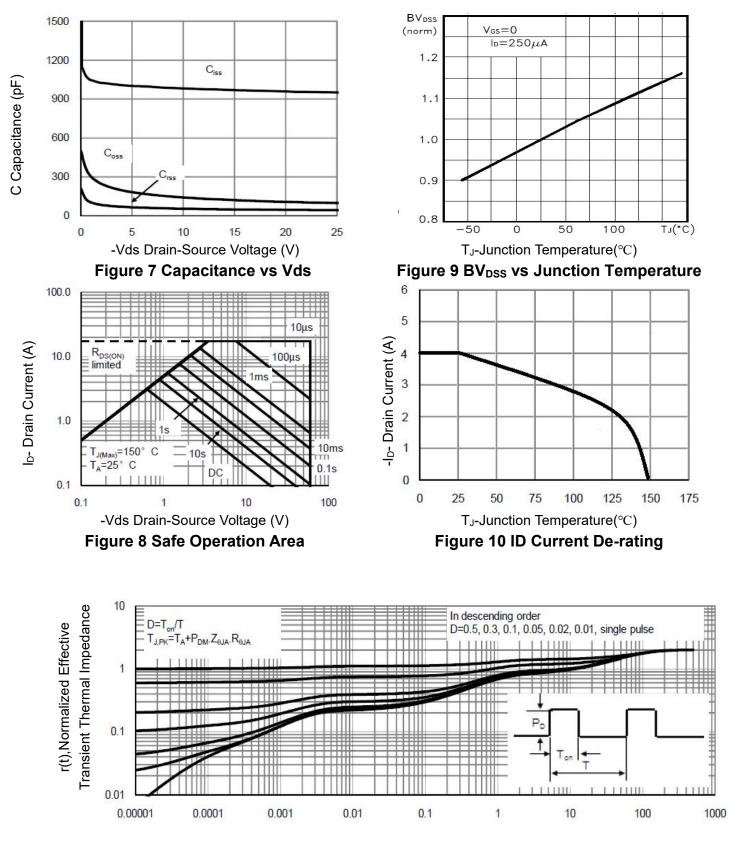






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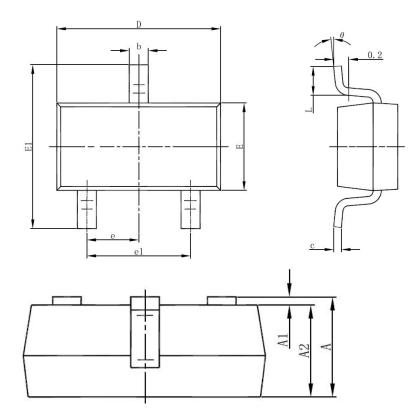
# NCE60P04Y



Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



## SOT-23-3L Package Information



Symbol	Dimensions Ir	n Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

#### Notes

1. All dimensions are in millimeters.

2. Tolerance ±0.10mm (4 mil) unless otherwise specified

3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.

4. Dimension L is measured in gauge plane.

5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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